Silicon NPN Epitaxial VHF / UHF wide band amplifier

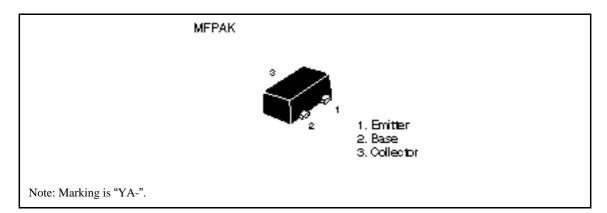
HITACHI

ADE-208-690 (Z) 1st. Edition Nov. 1998

Features

- Super compact package; $(1.4 \times 0.8 \times 0.59 \text{mm})$
- Capable low voltage operation ; $(V_{CE} = 1V) \label{eq:Vce}$

Outline



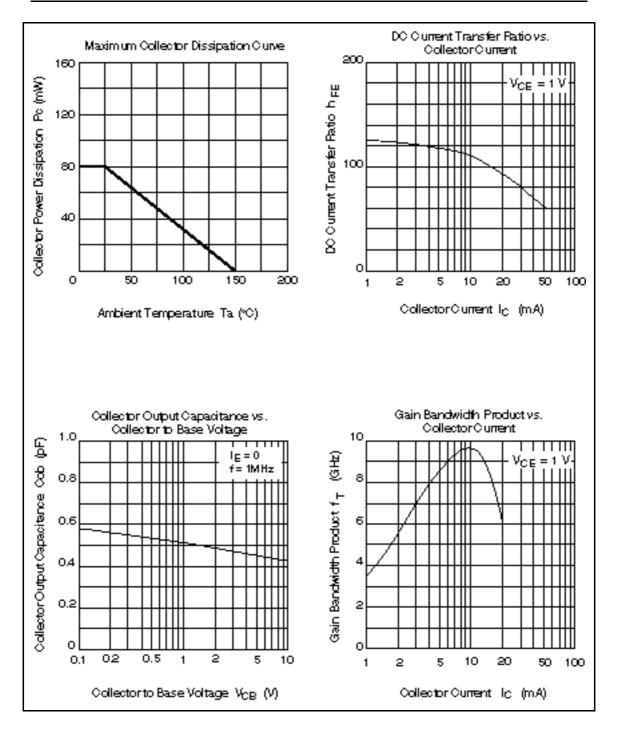


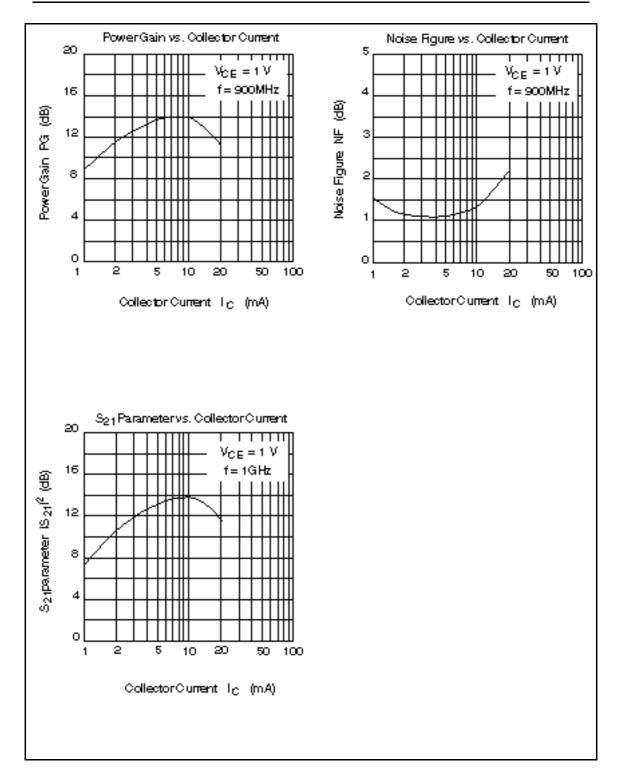
Absolute Maximum Ratings (Ta = 25° C)

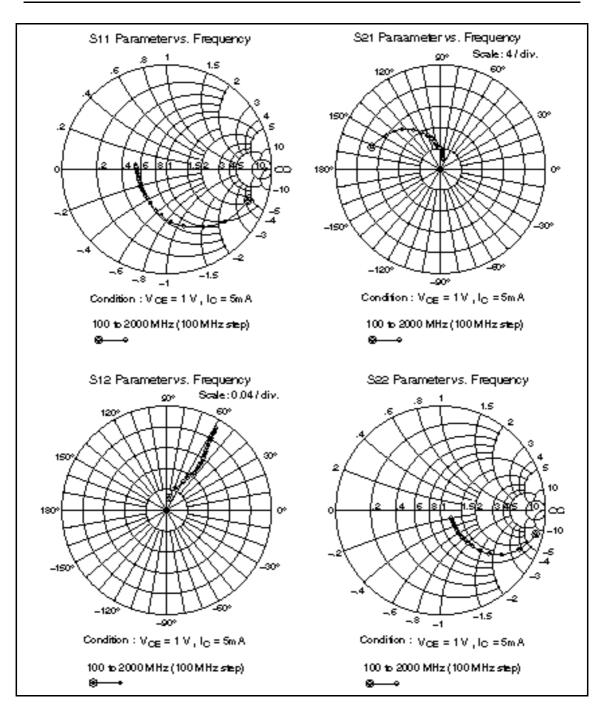
Item	Symbol	Ratings	Unit	
Collector to base voltage	V _{CBO}	15	V	
Collector to emitter voltage	V _{CEO}	8	V	
Emitter to base voltage	V _{EBO}	1.5	V	
Collector current	Ι _c	20	mA	
Collector power dissipation	Pc	80	mW	
Junction temperature	Tj	150	°C	
Storage temperature	Tstg	-55 to +150	°C	

Electrical Characteristics (Ta = 25°C)

Item	Symbol	Min	Тур	Max	Unit	Test Conditions
Collector cutoff current	I _{CBO}	_	_	10	μA	$V_{CB} = 15V$, $I_E = 0$
Collector cutoff current	I _{CEO}	_	_	1	mA	$V_{ce} = 8V$, $R_{be} =$
Emitter cutoff current	I _{EBO}	_	_	10	μA	$V_{_{\rm EB}}$ = 1.5V , $I_{_{\rm C}}$ = 0
DC current transfer ratio	h_{FE}	85		170	V	$V_{CE} = 1V$, $I_{C} = 5mA$
Collector output capacitance	Cob	_	0.51	0.9	pF	$V_{CB} = 1V$, $I_E = 0$ f = 1MHz
Gain bandwidth product	f_{T}	5.5	8.5	_	GHz	$V_{\rm CE}$ = 1V , $I_{\rm C}$ = 5mA
Power gain	PG	11	13.7	_	dB	$V_{CE} = 1V, I_C = 5mA$ f = 900MHz
Noise figure	NF	_	1.1	2.5	dB	$V_{CE} = 1V, I_C = 5mA$ f = 900MHz





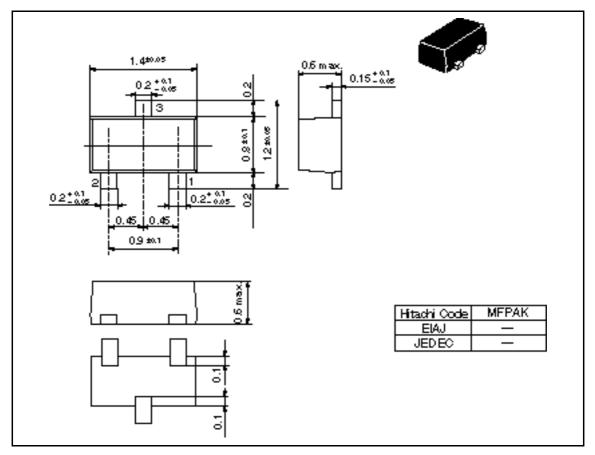


	S11		S21		S12		S22	
f (MHz)	MAG	ANG	MAG	ANG	MAG	ANG	MAG	ANG
100	0.836	-20.7	13.66	162.9	0.0249	77.4	0.948	-14.2
200	0.757	-41.1	12.22	146.9	0.0472	68.0	0.846	-26.9
300	0.649	-58.5	10.57	134.1	0.0637	60.8	0.727	-36.2
400	0.564	-73.2	9.14	124.5	0.0750	56.9	0.623	-42.5
500	0.496	-85.2	7.90	116.8	0.0840	54.2	0.538	-46.2
600	0.436	-97.1	6.91	111.2	0.0916	53.4	0.469	-48.8
700	0.396	-106.2	6.12	105.9	0.0985	53.0	0.413	-50.4
800	0.364	-114.9	5.49	102.0	0.105	53.2	0.368	-51.1
900	0.338	-123.9	4.96	98.3	0.111	53.6	0.327	-51.1
1000	0.316	-130.6	4.52	95.3	0.118	54.1	0.297	-51.2
1100	0.305	-140.0	4.16	92.3	0.124	54.7	0.270	-50.7
1200	0.296	-146.5	3.86	89.8	0.130	55.3	0.246	-49.7
1300	0.293	-153.0	3.59	87.5	0.137	56.1	0.229	-48.7
1400	0.286	-159.5	3.36	85.4	0.143	56.6	0.209	-47.9
1500	0.287	-166.0	3.17	83.2	0.150	57.2	0.195	-46.3
1600	0.285	-170.7	3.00	81.4	0.157	57.7	0.180	-45.0
1700	0.289	-175.8	2.83	79.8	0.164	58.2	0.167	-43.8
1800	0.294	178.7	2.71	77.9	0.171	58.8	0.154	-42.4
1900	0.302	175.4	2.59	75.9	0.178	59.0	0.144	-40.2
2000	0.308	171.1	2.47	74.5	0.185	59.2	0.133	-38.6

Sparameter (V $_{CE}$ = 1V, I_{C} = 5mA, Zo = 50 $\,$)

Package Dimensions

Unit: mm



Cautions

- 1. Hitachi neither warrants nor grants licenses of any rights of Hitachi's or any third party's patent, copyright, trademark, or other intellectual property rights for information contained in this document. Hitachi bears no responsibility for problems that may arise with third party's rights, including intellectual property rights, in connection with use of the information contained in this document.
- 2. Products and product specifications may be subject to change without notice. Confirm that you have received the latest product standards or specifications before final design, purchase or use.
- 3. Hitachi makes every attempt to ensure that its products are of high quality and reliability. However, contact Hitachi's sales office before using the product in an application that demands especially high quality and reliability or where its failure or malfunction may directly threaten human life or cause risk of bodily injury, such as aerospace, aeronautics, nuclear power, combustion control, transportation, traffic, safety equipment or medical equipment for life support.
- 4. Design your application so that the product is used within the ranges guaranteed by Hitachi particularly for maximum rating, operating supply voltage range, heat radiation characteristics, installation conditions and other characteristics. Hitachi bears no responsibility for failure or damage when used beyond the guaranteed ranges. Even within the guaranteed ranges, consider normally foreseeable failure rates or failure modes in semiconductor devices and employ systemic measures such as fail-safes, so that the equipment incorporating Hitachi product does not cause bodily injury, fire or other consequential damage due to operation of the Hitachi product.
- 5. This product is not designed to be radiation resistant.
- 6. No one is permitted to reproduce or duplicate, in any form, the whole or part of this document without written approval from Hitachi.

http:semiconductor.hitachi.com/

http://www.hitachi-eu.com/hel/eog

7. Contact Hitachi's sales office for any questions regarding this document or Hitachi semiconductor products.

: http://www.has.hitachi.com_sg/grp3/sicdindex.htm : http://www.hitachi.com_tw/B/ProductSICD_Frame.htm : http://www.hitachi.com_hk/eng/bo/grp3/index.htm : http://www.hitachi.co.jp/Sicdindx.htm

HITACHI

Hitachi, Ltd. Semicorductor & IC Div

NipponBidt, 24-2 Ohle-madri, Chiyoda-ku, Tokyo 100.0004, Japan Tel: Tokyo (03) 3270-2111 Fax: (03) 3270-5109

URL North America Europe Asia (Singapore) Asia (Taivan) Asia (HongKong) Japan

For further information write to: His dri Semiconductor His dri Education (America) Inc. 2000 Sieme Point Perlawy Briebana OL 94005 1901 Germany Fait of b (200) 225-1601 Germany Fait of b (200) 227-0447 Tel: c406 (8)

Hachi Europe GnbH Betronic componente Group Donecher Stellerö D35522 Feldlichen, Munich Germany Tel: c456 (30) 9 9180-0 Fex c456 (30) 9 29 30 00 Hachi Europe Lti. Betronic Componente Group. Whitebrock Park Lower Cookhern Roed Meidenheed Berlehine SL6370, United Kingdom Tel: c446 (1628) 555000 Fex c440 (1628) 778322

Hischi Arin Pos Ltd. 16 Colyer Gauy 820-00 Hischi Tower Sagepore 048018 Tel: 535-2100 Rev: 535-1533

Hinchi Asin Lel. Taipei Brunch Office 3°, Hung Kuo Buiking, Na 167, Tun Hwa Noth Road, Taipei (105) Tel: c886c (2) 2718-3685 Fax: c886c (2) 2718-3180 Hischi Arin (Hong Kong) Ltd. Group III (Biedronic Componente) 7/F., North Tower, World Finence Centre, Harbour Oby, Onnine Roed, Teim Ste Teui, Kowloon, Hong Kong Tel: 28222 (2) 735 92 18 Fax 28225 (2) 735 92 18 Tele: 408 15 HITECHX

Copyright @Hitschi, Ltd., 1998. All rights reserved. Printed in Japan.